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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of  
Richard A. Soref et al  
Application Serial No. 10/722,611  
Filed: 28 November 2003

Group Art Unit: 2815  
Examiner: Allan Wilson

For: **STRAIN-ENGINEERED DIRECT-GAP  $\text{Ge/Sn}_x\text{Ge}_{1-x}$  HETERODIODE AND  
MULTI-QUANTUM-WELL PHOTODETECTORS, LASERS, EMITTERS AND  
MODULATORS GROWN ON  $\text{Sn}_y\text{Si}_z\text{Ge}_{1-y-z}$ -BUFFERED SILICON**

Honorable Commissioner of Patents  
Alexandria, VA. 22313-1450

Sir:

TERMINAL DISCLAIMER

Your petitioner, the U.S. Government as represented by the Secretary of the Air Force, represents that it is the assignee of the entire right, title and interest in and to the above-identified patent Application Serial No. 10/722,611 filed on 28 November 2003 as well as U.S. Patent 5,548,128.

Your petitioner, the U.S. Government as represented by the Secretary of the Air Force, hereby disclaims the terminal part of any patent granted on the above-identified Application Serial No. 10/722,611, which would extend beyond the expiration date of U.S. Patent No. 5,548,128, and hereby agrees that any patent so granted on the above-identified Application Serial No. 10/722,611 shall be enforceable only for during said period that the legal title to said

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